

**Le87271**  
**Datasheet**  
**xDSL CPE Line Driver**

Preliminary  
August, 2019



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# 1 Revision History

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The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

## 1.1 Revision 3.0

Revision 3.0 of this document was published in August 2019. The following is a summary of the changes.

- Features and applications of the Le87271 device were updated. For more information, see the [Product Overview \(see page 2\)](#) section.
- Section [Output Driving Considerations \(see page 12\)](#) was edited.

## 1.2 Revision 2.0

Moved from Advance to Preliminary.

## 1.3 Revision 1.0

Revision 1.0 was published in December 2018. Revision 1.0 was the first publication of this document.

## 2 Product Overview

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The Le87271 device is a single-channel differential amplifier designed to work in Customer Premise Equipment (CPE) systems. It provides multiple bias levels to optimize power and performance. In addition, the line driver features a power-down state, which forces low power. The control pins respond to input levels that can be generated with a standard GPIO.

The Le87271 device is available in a 20-pin (4 mm x 4 mm) QFN package with an exposed pad for enhanced thermal conductivity.

### 2.1 Features

The Le87271 device has the following important features:

- High-power differential output
  - Delivers line power up to 14 dBm
  - Operates at 14 V  $\pm$ 10 %
- Class AB amplifiers
- Four biased up states for VDSL applications
- Four biased up states for ADSL applications
- Power down states
- Thermal shutdown circuitry
- Miniature 4 mm x 4 mm thermally enhanced package
- RoHS compliant

### 2.2 Applications

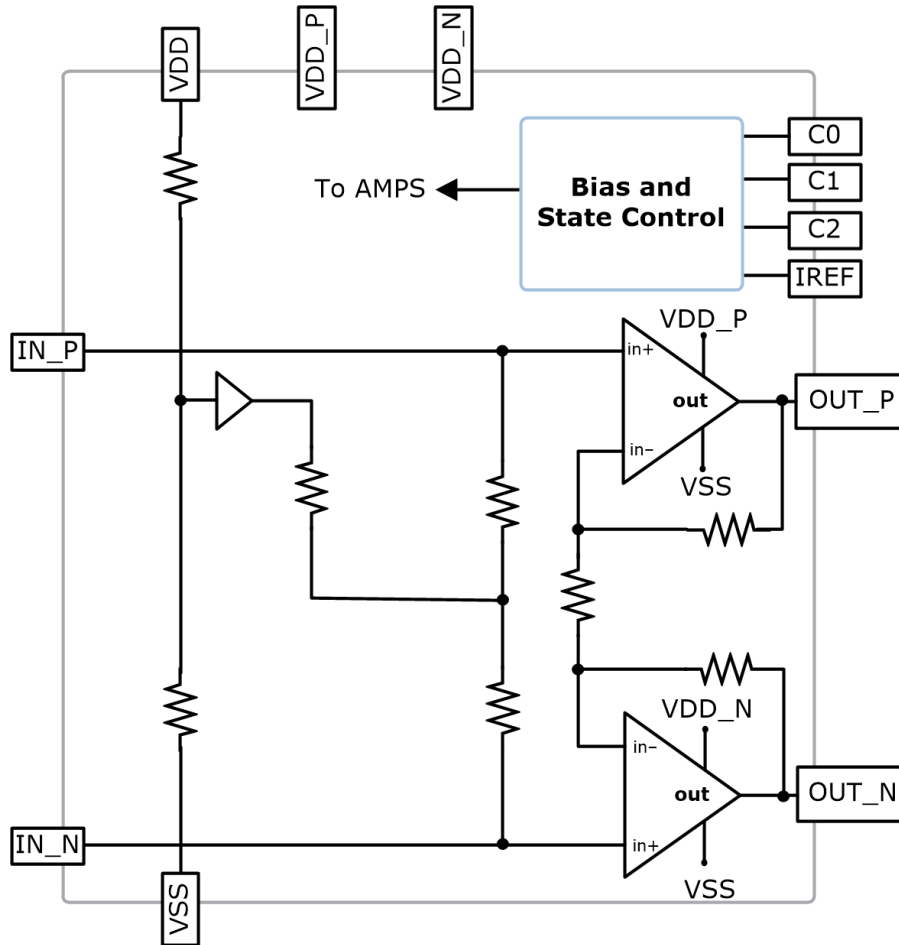
The following applications use the Le87271 device.

- CPE Line Driver for ADSL, ADSL2, and ADSL2+
- CPE Line Driver for VDSL2, all profiles up to 17a, 30a, and 35b.

## 2.3 Block Diagram

The following figure shows the Le87271 block diagram.

Figure 1 • Line Driver Block Diagram

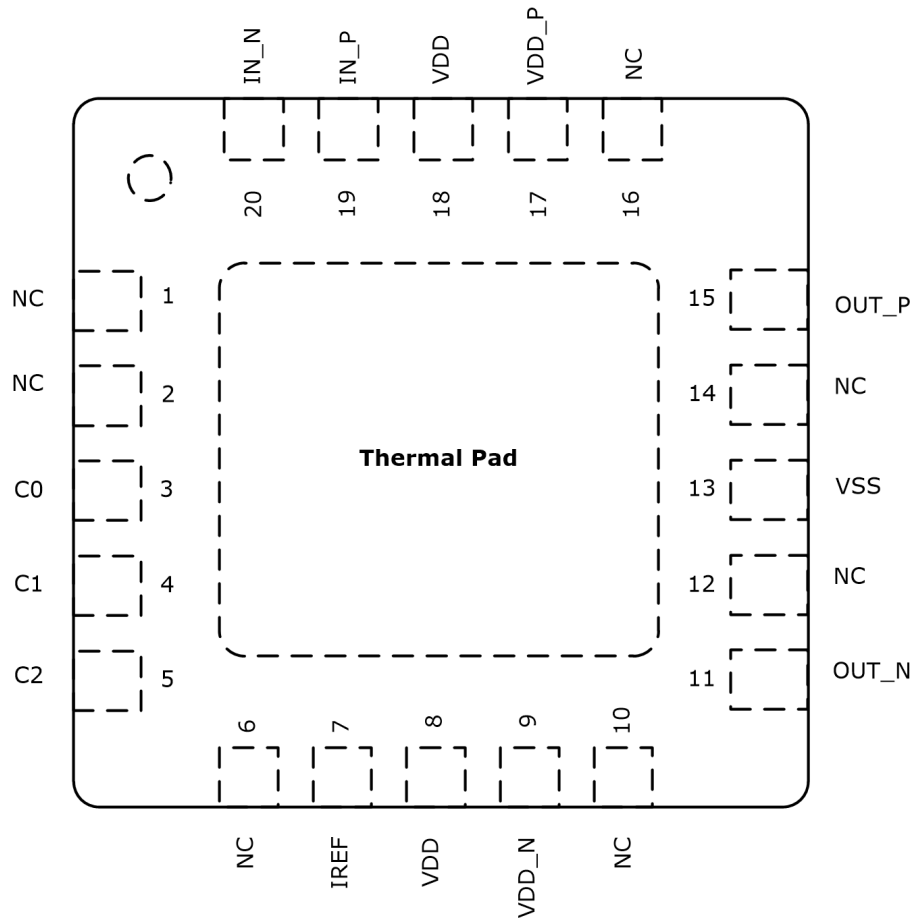


### 3 Pin Descriptions

The Le87271 device has 20 pins that are described in the following section.

The following figure shows the top-view of the Le87271 pin configuration.

**Figure 2 • Pin Diagram**



**Note:** The device incorporates an exposed die pad on the underside of its package. The pad acts as a heat sink and must be connected to a copper plane through the thermal plane for proper heat dissipation. It is internally connected to VSS, but on the board, it should be connected to ground.

### 3.1 Pin Description

The following table lists the functional pin descriptions of the Le87271 device.

**Table 1 • Pin Descriptions**

Pin	Pin Name	Pin Type	Description
1	NC		No connects, no internal connection
2	NC		No connects, no internal connection
3	C0	Input	Logic level inputs for state control
4	C1	Input	Logic level inputs for state control
5	C2	Input	Logic level inputs for state control
6	NC		No connects, no internal connection
7	IREF		Bias current reference
8	VDD		Power supply
9	VDD_N		Power supply
10	NC		No connects, no internal connection
11	OUT_N	Output	Line driver differential output
12	NC		No connects, no internal connection
13	VSS	Ground	Ground
14	NC		No connects, no internal connection
15	OUT_P	Output	Line driver differential output
16	NC		No connects, no internal connection
17	VDD_P		Power supply
18	VDD		Power supply
19	IN_P	Input	Line driver differential input
20	IN_N	Input	Line driver differential input

## 4 Electrical Specifications

The following section shows the electrical specifications of the Le87271 device.

### 4.1 Absolute Maximum Ratings

The following section shows the absolute maximum ratings, thermal resistance, and operating ranges of the Le87271 device.

The following table lists the absolute maximum ratings of the Le87271 device.

**Table 2 • Absolute Maximum Ratings**

Names	Range	Unit
VDD with respect to VSS	−0.3 to 16	V
Control inputs with respect to VSS	−0.3 to 4	
Junction temperature	−40 to 150	°C
ESD immunity (Human Body Model)	JESD22 Class 2 complaint	
ESD immunity (Charge Body Model)	JESD22 class IV compliant	

Continuous operation above 145 °C junction temperature may degrade the device reliability. The typical TSD temperature is 170 °C, with 20 °C hysteresis.

#### 4.1.1 Thermal Resistance

Thermal performance of a thermally enhanced package is assured through an optimized PCB layout. The specified performance requires that the exposed thermal pad should be soldered to an equally sized exposed copper surface, which, in turn, conducts heat through multiple vias to larger internal copper planes.

The following table lists the simulation results of a device mounted on a 4-layer JEDEC PCB with 12 thermal vias in still air. These numbers are only for reference.

**Table 3 • Thermal Resistance Specifications**

Names	Value	Unit
Maximum device power dissipation, continuous - $T_A = 150$ °C	1.37	W
Junction to ambient thermal resistance, $\theta_{JA}$	47.5	°C/W
Junction-to-board thermal resistance, $\theta_{JB}$	25.8	
Junction-to-case bottom (exposed pad) thermal resistance, $\theta_{JP}$	11.7	
Junction-to-top characterization parameter, $\theta_{JC}$	30.8	

#### 4.1.2 Package Assembly

Green package devices are assembled with enhanced, environmental-friendly lead-free, halogen-free, and antimony-free materials. The leads possess a matte-tin plating, which is compatible with conventional board assembly processes or newer lead-free board assembly processes.



See IPC/JEDEC J-Std-020 for recommended peak soldering temperature and solder re-flow temperature profile.

### 4.1.3 Operating Ranges

Microsemi guarantees the performance of this device over the  $-40\text{ }^{\circ}\text{C}$  to  $85\text{ }^{\circ}\text{C}$  temperature range by conducting electrical characterization and a single insertion production test coupled with periodic sampling. These procedures comply with the Telcordia GR-357-CORE generic requirements for assuring the reliability of components used in telecommunications equipment.

The following table lists the operating ranges used in this device.

**Table 4 • Operating Ranges**

Name	Unit	Minimum	Typical	Maximum
Supply voltage, VDD/VDD_P/VDD_N	V	12.6	14	15.4
Ambient temperature	$^{\circ}\text{C}$	$-40$	25	85
Line impedance	$\Omega$	80	100	150

## 4.2 Device Specifications

The following section shows the DC characteristics, AC characteristics, and recommended operating conditions of the Le87271 device.

Typical values are characteristics of the Le87271 device and are the result of the engineering evaluation. Minimum and maximum values apply across the operating temperature range and the entire supply range does not vary unless otherwise specified.

**Note:** Typical values are for information purposes only and are not part of the testing requirement.

**Typical Conditions:** VDD = VDD\_P = VDD\_N = 14 V; RL = 50  $\Omega$  differential load; RREF = 75 k $\Omega$ ; TA = 25  $^{\circ}\text{C}$ . For more information, see the [Basic Test Circuit \(see page 9\)](#) figure.

The following table lists the electrical specifications. As VDD, VDD\_P, and VDD\_N are expected to be tied together, IVDD represents the total current through these three pins, and PVDD represents the total supply power.

**Table 5 • Electrical Specifications**

Symbol	Parameter Description	Condition	Min	Typ	Max	Unit	Note
IVDD	Quiescent supply current	ATX4	14.8	17.4	20.0	mA	
IVDD	Quiescent supply current	ATX3	13.3	15.6	17.9	mA	
IVDD	Quiescent supply current	ATX2	10.7	12.6	14.5	mA	
IVDD	Quiescent supply current	ATX1	9.4	11.0	12.7	mA	

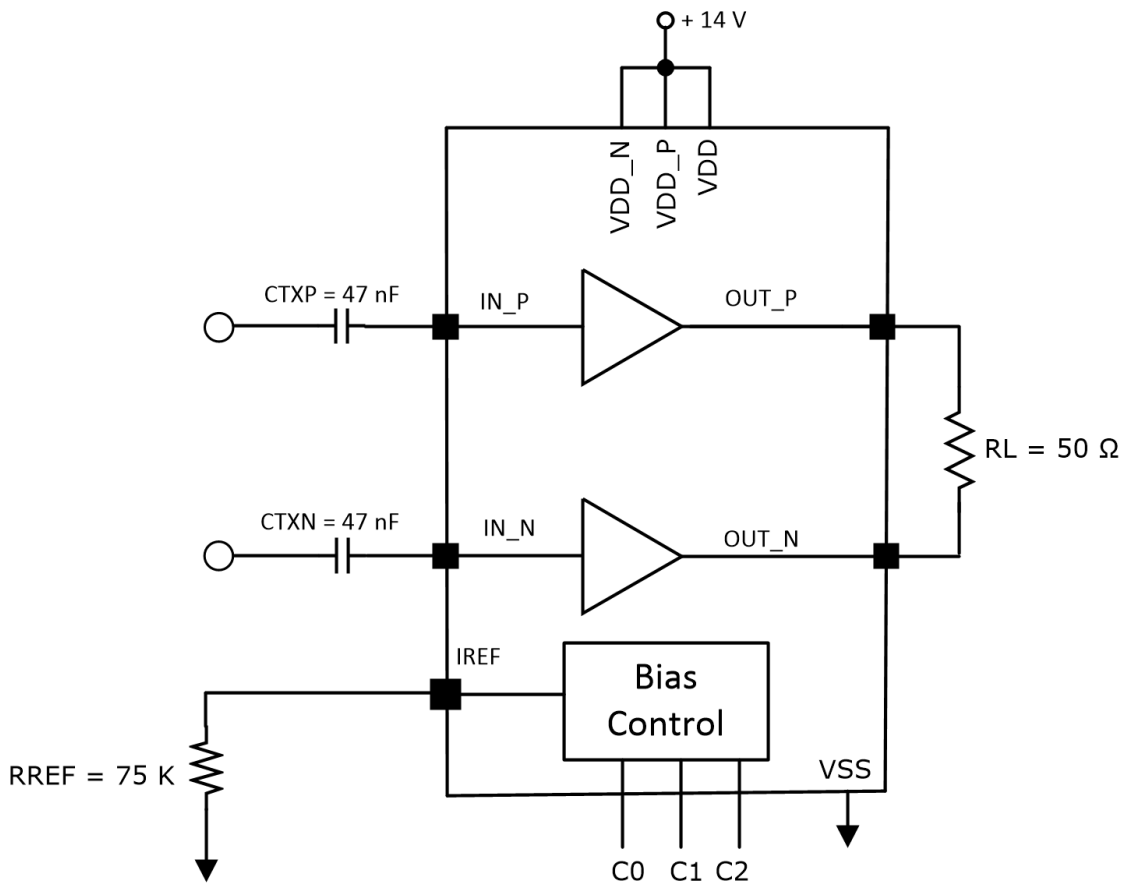
Symbol	Parameter Description	Condition	Min	Typ	Max	Unit	Note
IVDD	Quiescent supply current	VTX4	19.3	22.7	26.1	mA	
IVDD	Quiescent supply current	VTX3	17.8	20.9	24.0	mA	
IVDD	Quiescent supply current	VTX2	15.1	17.8	20.5	mA	
IVDD	Quiescent supply current	VTX1	13.7	16.1	18.5	mA	
PVDD	Supply power	PLine = 13 dBm			600	mW	1
V <sub>OUT</sub>	Output voltage	Between OUT_P/N	10.5			V <sub>pkd</sub>	
I <sub>OUT</sub>	Drive current	Through OUT_P/N	240			mA <sub>pk</sub>	2
i <sub>N</sub>	Input-referred noise	VTX States			6	nV/rtHz	1
i <sub>N</sub>	Input-referred noise	ATX States			4	nV/rtHz	1
AV	Gain		7.88	8.03	8.20	V/V	
BW	Bandwidth	-3 dB, ATX4 States		146		MHz	1
BW	Bandwidth	-3 dB, ATX3 States		140		MHz	1
BW	Bandwidth	-3 dB, ATX2 States		90		MHz	1
BW	Bandwidth	-3 dB, ATX1 States		72		MHz	1
BW	Bandwidth	-3 dB, VTX4 States		200		MHz	1
BW	Bandwidth	-3 dB, VTX3 States		190		MHz	1
BW	Bandwidth	-3 dB, VTX2 States		148		MHz	1
BW	Bandwidth	-3 dB, VTX1 States		137		MHz	1
AVF	Gain flatness	f < Signal BW	-0.3		0.3	dB	1, 3
MTPR	Missing tone power ratio	VDSL, PAR = 6.8	64			dBc	1
MTPR	Power ratio	ADSL, PAR = 6.3	90			dBc	1
RI	Input impedance	Differential	12	15	18	kΩ	
RO	Output impedance	Differential	0		1	Ω	1
CMRR	Common mode rejection ratio	f < Signal BW		35		dB	1, 3
PSRR	Power supply rejection ratio	f < Signal BW	50			dB	1, 3
IVDD	Quiescent supply current	Power down state	0.4	0.6	0.8	mA	
ON	Output noise	Power down state (100 kHz–30 MHz)		0.9		nV/rtHz	1
RO	Output impedance	Power down state (Differential)		680		Ω	1
VIH	Input high voltage		2.0			V	
VIL	Input low voltage				0.8	V	
VIM	Input middle voltage	C0	1.4	1.5	1.6	V	
I <sub>IH</sub>	Input high current	VIH = 3 V, C0	15	50	85	μA	

Symbol	Parameter Description	Condition	Min	Typ	Max	Unit	Note
I <sub>IH</sub>	Input high current	V <sub>IH</sub> = 3 V, C1, C2	60	120	180	μA	
I <sub>IL</sub>	Input low current	V <sub>IL</sub> = 0 V, C0	-85	-50	-15	μA	
I <sub>IL</sub>	Input low current	V <sub>IL</sub> = 0 V, C1, C2	-2	0	2	μA	
Z <sub>in</sub>	Logic input impedance			25		kΩ	

**Notes:**

1. Not tested in production. Guaranteed by design and characterization.
2. For line impedance of 80 Ω.
3. Frequency range within signal bandwidth is 552 kHz for ADSL and 30 MHz for VDSL.

The following figure shows the basic test circuit of the Le87271 device.

**Figure 3 • Basic Test Circuit**

## 4.3 Operational States

Operating state is controlled through three input pins: C0, C1, and C2. C1 and C2 are binary inputs with internal pull-down resistors. C0 is a tri-state input with an internal resistor pulling to the middle (M) logic value if the pin is not driven. If the inputs are not driven, the line driver by default changes into the power down state.

The following table lists the operational state control of the Le87271 device.

**Table 6 • Operational State Control**

C2	C1	C0	State	Device State
H	H	M	ATX4	Low noise for ADSL
H	L	H	ATX3	Low noise for ADSL
H	H	L	ATX2	Low noise for ADSL
H	H	H	ATX1	Low noise for ADSL
L	H	M	VTX4	High speed for VDSL
L	L	H	VTX3	High speed for VDSL
L	H	L	VTX2	High speed for VDSL
L	H	H	VTX1	High speed for VDSL
X	L	L	Power down	Amplifiers off, high impedance outputs
X	L	M	Power down	Amplifiers off, high impedance outputs
X	X	X	Thermal shut-down	Amplifiers off, high impedance outputs

### 4.3.1 TX States

In TX states, the amplifiers are fully active with gain from IN<sub>x</sub> to OUT<sub>x</sub>. TX states provide four steps of bias current to the amplifiers. This allows some selection of power versus linearity in the line driver performance. The TX states are further identified as ADSL states (lower bias current, lower noise) or VDSL states (higher bias current, higher bandwidth).

### 4.3.2 Power Down State

Line driver amplifiers are turned off, and there is no gain from IN<sub>x</sub> to OUT<sub>x</sub>. The amplifier outputs are high-impedance. The gain-setting resistors around the amplifiers remain in place and present a differential impedance at the OUT\_P/N.

### 4.3.3 Thermal Shut-down

Thermal shut-down (TSD) is activated at high silicon temperature. Amplifiers are turned off. There is hysteresis in the TSD temperature threshold. After the silicon cools down below the threshold level, the line driver returns to the operating state indicated by the control inputs.

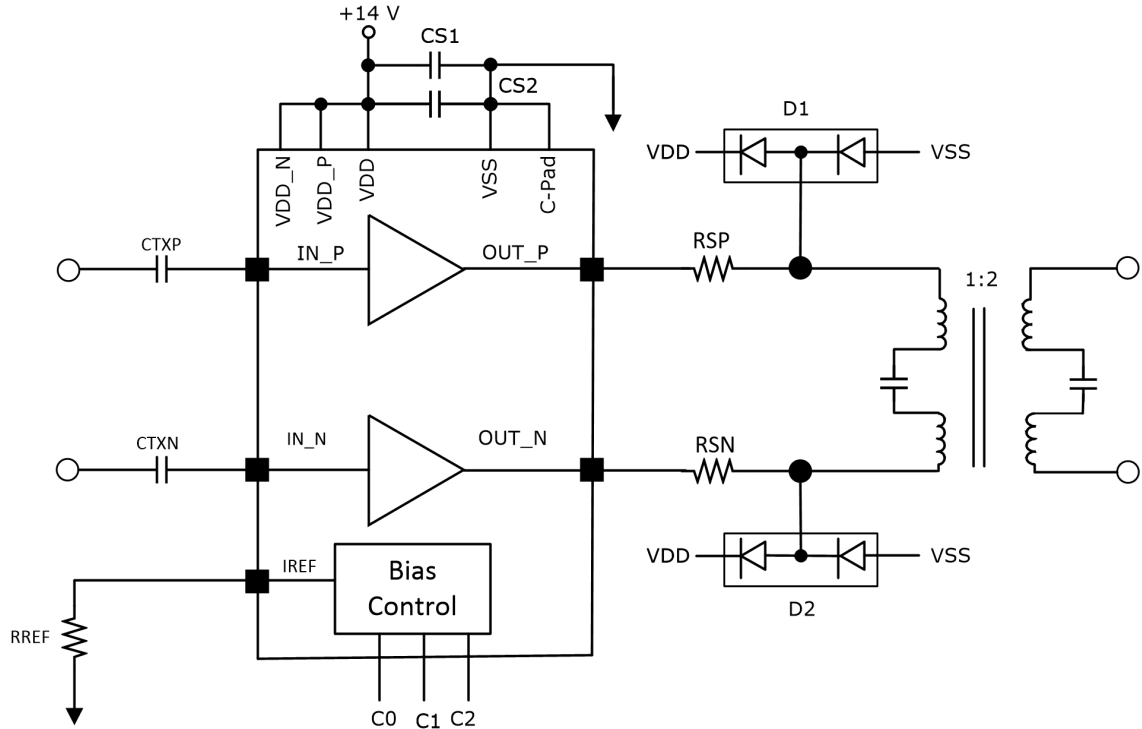
## 5 Applications

This section shows the applications that use the Le87271 device, and the block diagram describe the functionalities.

### 5.1 Typical Application Circuits

The following figure shows the typical application circuit of the Le87271 device.

Figure 4 • Typical Application Circuit



The following table lists the resistors and capacitors with the tolerance values.

Table 7 • Application Circuit Names and Values

Names	Type	Value	Unit	Tolerance	Rating
RREF	Resistor	75.0	k $\Omega$	1%	0402
RSP	Resistor	12.4	$\Omega$	1%	0805
RSN	Resistor	12.4	$\Omega$	1%	0805
CS1	Capacitor	1	$\mu$ F	20%	X7R, 25 V
CS2	Capacitor	0.01	$\mu$ F	20%	X7R, 25 V
D1	Diode Bridge	BAV99			
D2	Diode Bridge	BAV99			
CTXP	Capacitor	0.047	$\mu$ F	20%	X7R, 25 V
CTXN	Capacitor	0.047	$\mu$ F	20%	X7R, 25 V

### 5.1.1 IREF

Connect RREF from IREF pin to ground. DC current through RREF provides reference bias current for the device.

### 5.1.2 Input Consideration

The inductance of the trace from driving source to CTXP or CTXN should be less than 100 nH to avoid any ringing or oscillation.

### 5.1.3 Output Driving Considerations

Inside the amplifier, there is no current limit mechanism. RSA and RSB in a few ohms enable to limit current viewed by the line driver in case of large fault transients. If a DC current path exists between the two outputs, DC current can flow through the outputs. With RSP and RSN resistors as shown in place, however, any DC current will be trivial, and therefore, such DC blocking capacitor may not be needed.

### 5.1.4 Protection

The line driver has thermal shutdown protection. Amplifiers turn off and outputs appear as high-impedance if the silicon temperature rises above the TSD temperature.

As shown in the [Typical Application Circuit \(see page 11\)](#) figure, diode bridges may be used at the secondary side of the data transformer to clamp transients between the VDD and VSS rails. It is possible that additional transient clamping devices are needed to protect on the line side of the data transformer the isolation of the data transformer in the event of common mode faults.

### 5.1.5 Power Supplies and Component Placement

The power supply should be well bypassed with decoupling placed close to the Le87271 device.

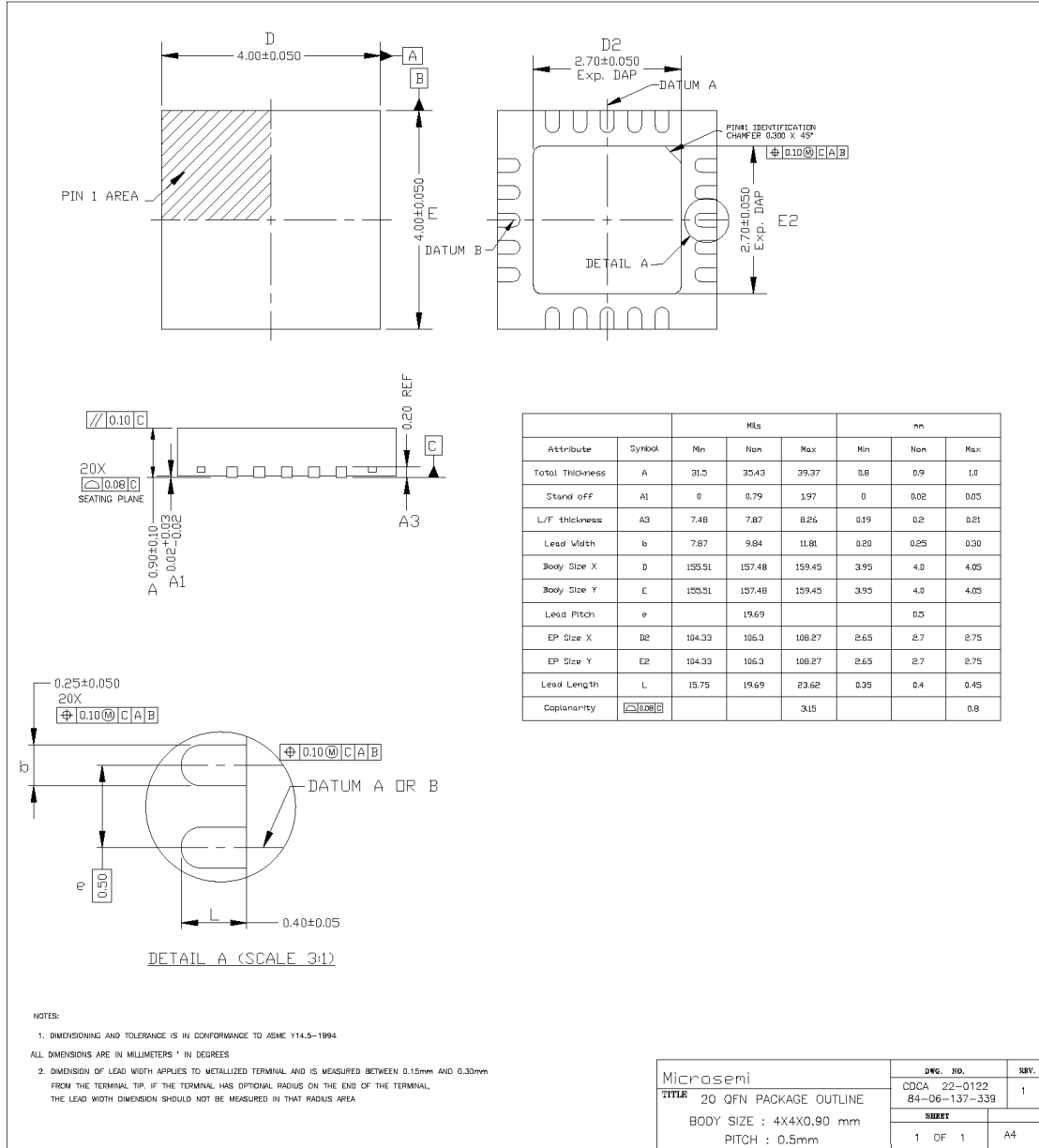
## 6 Package Specifications

This section shows the package information of the Le87271 device.

### 6.1 Physical Dimension - 20-Pin Diagram

The following figure shows the package drawing for the Le87271 device. The drawing contains the top, bottom, and side views.

Figure 5 • Physical Dimension - 20 Pins



**Note:** Packages might have mold tooling markings on the surface. These markings have no impact on the form, fit, or function of the device. Markings vary with the mold tool used during manufacturing.

## 7 Ordering Information

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The following table lists the ordering information of Le87271.

Part Order Number	Description	Packing System
Le87271EQC	20-pin, 4mm x 4mm QFN green package with an exposed pad	Tray
Le87271EQCT	20-pin, 4mm x 4mm QFN green package with an exposed pad	Tape and reel

**Note:** The green package is halogen free and meets the RoHS2 directive 2011/65/EU of the European Council to minimize the environmental impact of electrical equipment.



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